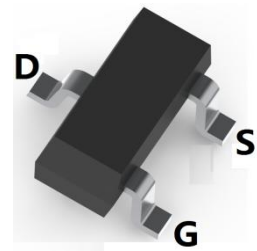
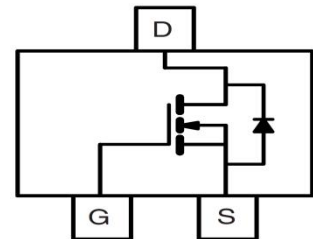


**HIGH VOLTAGE MOSFET (N-CHANNEL)**
**FEATURES**

- $V_{DS}=100V, R_{DS(ON)}=6\Omega @ V_{GS}=10V, I_D=0.17A$
- High Density Cell Design for Extremely Low  $R_{DS(ON)}$
- Voltage Controlled Small Signal Switch
- For Small Servo Motor Controls, Power MOSFET Gate Drivers And Switching Applications
- Surface Mount device


**SOT-23**

**MECHANICAL DATA**

- Case: SOT-23
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.008 grams (approximate)

**MAXIMUM RATINGS ( $T_A = 25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	100	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current	$I_D$	0.17	A
Pulsed drain current	$I_{DM}$	0.68	A
Continous Source-Drain Diode Current	$I_S$	0.17	A
Power dissipation	$P_D$	0.35	W
Thermal resistance from Junction to ambient	$R_{\theta JA}$	357	$^\circ C/W$
Junction temperature	$T_J$	150	$^\circ C$
Storage temperature	$T_{STG}$	-55 ~ +150	$^\circ C$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	$T_L$	260	$^\circ C$

**ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ C$  unless otherwise specified)**

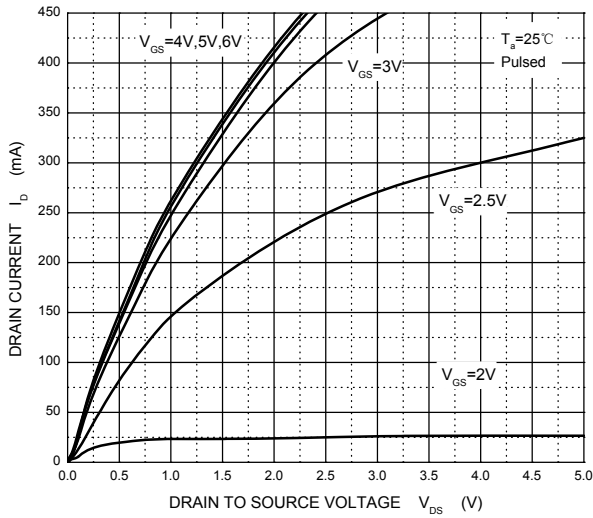
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
<b>STATIC CHARACTERISTICS</b>						
Drain-Source breakdown voltage	$V_{(BR)DSS}$	100			V	$V_{GS}=0V, I_D=250\mu A$
Zero gate voltage drain current	$I_{DSS}$			1	$\mu A$	$V_{DS}=100V, V_{GS}=0V$
				10	nA	$V_{DS}=20V, V_{GS}=0V$
Gate-body leakage current	$I_{GSS}$			$\pm 50$	nA	$V_{DS}=0V, V_{GS}=\pm 20V$
Gate-threshold voltage (note 1)	$V_{GS(th)}$	1	1.6	2.8	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Drain-source on-resistance (note 1)	$R_{DS(ON)}$		3.8	10	$\Omega$	$V_{GS}=4.5V, I_D=0.17A$
			3.5	6	$\Omega$	$V_{GS}=10V, I_D=0.17A$
Forward trans-conductance (note 1)	$g_{FS}$	80			mS	$V_{DS}=10V, I_D=0.17A$
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=0.34A, V_{GS}=0V$
<b>DYNAMIC CHARACTERISTICS</b>						
Input capacitance	$C_{iss}$		29	60	pF	$V_{DS}=25V, V_{GS}=0V, f=1MHz$
Output capacitance	$C_{oss}$		10	15	pF	
Reverse transfer capacitance	$C_{rss}$		2	6	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-on delay time	$t_{d(on)}$			8	nS	$V_{DD}=30V, V_{GS}=10V, R_{GEN}=50\Omega, I_D=0.28A$
Turn-on rise time	$t_r$			8	nS	
Turn-off delay time	$t_{d(off)}$			13	nS	
Turn-off fall time	$t_f$			16	nS	
Total gate charge	$Q_g$		1.4	2	nC	$V_{DS}=10V, V_{GS}=10V, I_D=0.22A$
Gate-source charge	$Q_{gs}$		0.15	0.25	nC	
Gate-drain charge	$Q_{gd}$		0.2	0.4	nC	

Note:1. Pulse test ; Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$  .

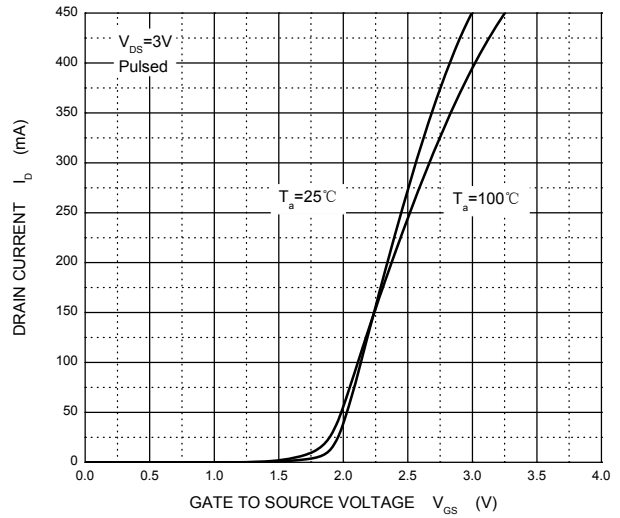
**HIGH VOLTAGE MOSFET (N-CHANNEL)**

**Typical Characteristics**

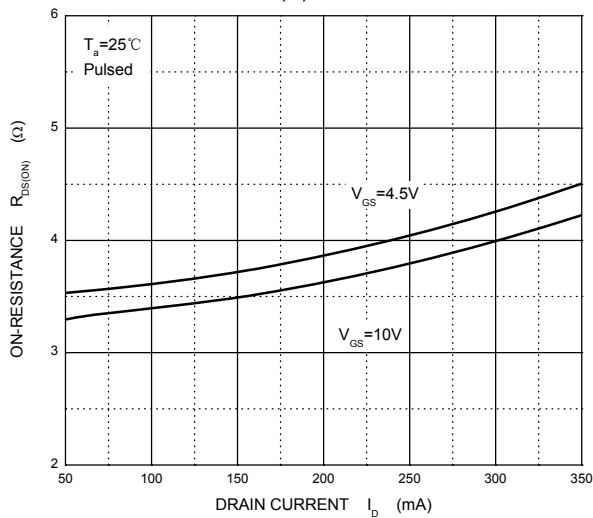
**Output Characteristics**



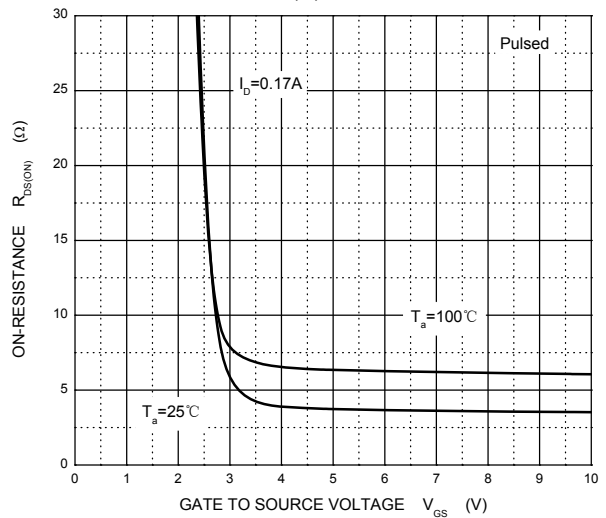
**Transfer Characteristics**



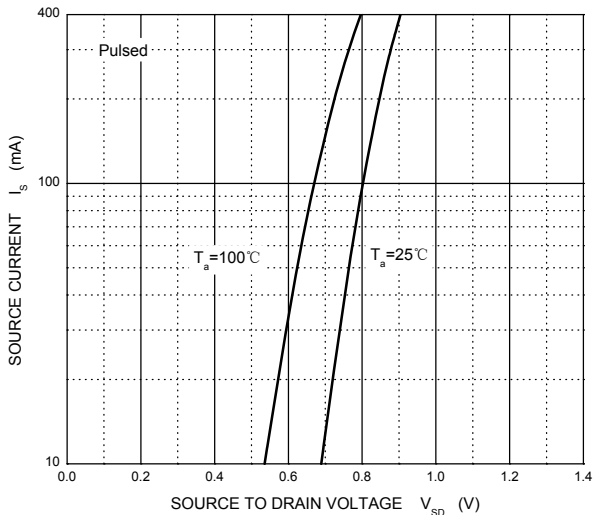
**$R_{DS(ON)}$  —  $I_D$**



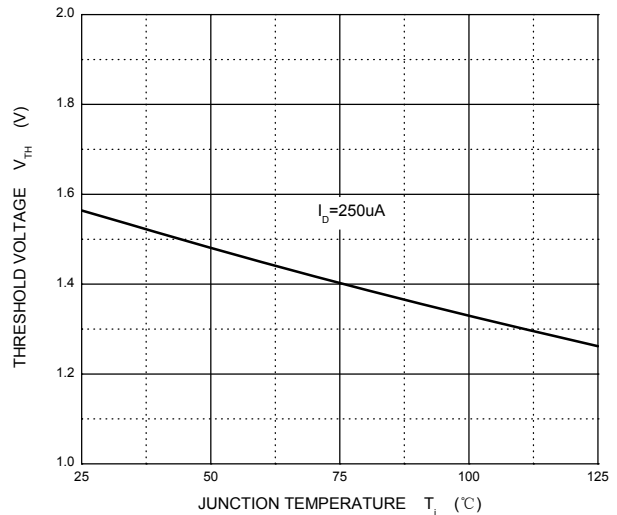
**$R_{DS(ON)}$  —  $V_{GS}$**



**$I_S$  —  $V_{SD}$**



**Threshold Voltage**



HIGH VOLTAGE MOSFET (N-CHANNEL)

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



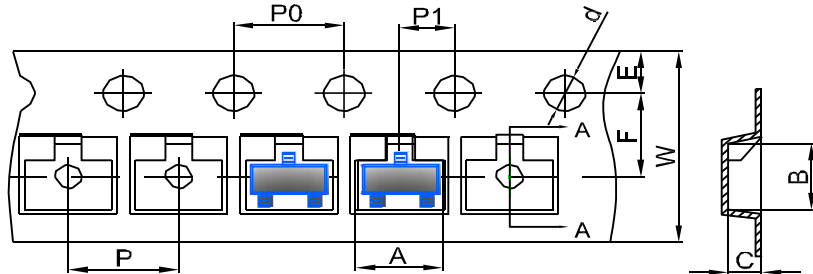
**Note:**

1. Controlling dimension: in millimeters
2. General tolerance: ±0.05mm
3. The pad layout is for reference purposes only

**HIGH VOLTAGE MOSFET (N-CHANNEL)**

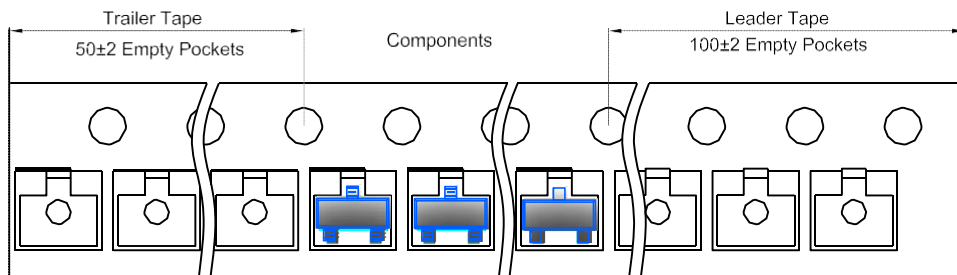
**SOT-23 Tape and Reel**

**SOT-23 Embossed Carrier Tape**

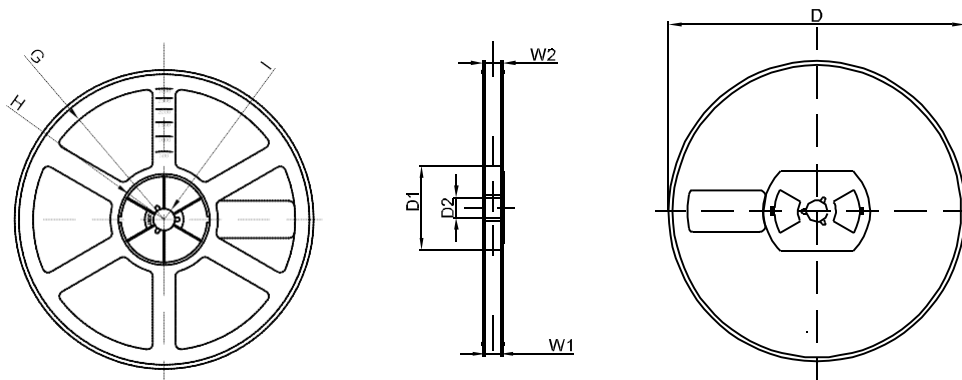


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

**SOT-23 Tape Leader and Trailer**



**SOT-23 Reel**



DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [Hottech](#) manufacturer:*

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [NTNS3A92PZT5G](#) [IRFD120](#) [IRFF430](#) [JANTX2N5237](#) [2N7000](#) [AOD464](#)  
[2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#)  
[IPS70R2K0CEAKMA1](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#)  
[EFC2J004NUZTDG](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMC2700UDMQ-7](#)  
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#)  
[DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [IPSA70R950CEAKMA1](#) [IPSA70R2K0CEAKMA1](#) [STU5N65M6](#)  
[C3M0021120D](#) [DMN6022SSD-13](#)